3 W DO-41 Surmetic[™] 30 Zener Voltage Regulators

This is a 1N59xxBRNG series with limits and excellent operating characteristics that reflect the superior capabilities of silicon-oxide passivated junctions. All this in an axial-lead, transfer-molded plastic package that offers protection in all common environmental conditions.

Features

- Zener Voltage Range 3.3 V to 200 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Surge Rating of 98 W @ 1 ms
- Maximum Limits Guaranteed on up to Six Electrical Parameters
- Package No Larger than the Conventional 1 W Package
- This is a Pb–Free Device

Mechanical Characteristics

CASE: Void free, transfer–molded, thermosetting plastic **FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 260°C, 1/16" from the case for 10 seconds POLARITY: Cathode indicated by polarity band MOUNTING POSITION: Any

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ T ₁ = 75°C, Lead Length = 3/8"	PD	3.0	W
Derate above 75°C		24	mW/°C
Steady State Power Dissipation @ $T_A = 50^{\circ}C$	PD	1.0	W
Derate above 50°C		6.67	mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com



MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
1N59xxBRNG	Axial Lead (Pb-Free)	3000 Units / Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS

 $(T_L = 30^{\circ}C \text{ unless otherwise noted}, V_F = 1.5 V \text{ Max } @ I_F = 200 \text{ mAdc for all types})$

Symbol	Parameter			
VZ	Reverse Zener Voltage @ I _{ZT}			
I _{ZT}	Reverse Current			
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}			
I _{ZK}	Reverse Current			
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}			
I _R	Reverse Leakage Current @ V _R			
V _R	Breakdown Voltage			
١ _F	Forward Current			
V _F	Forward Voltage @ I _F			
I _{ZM}	Maximum DC Zener Current			



		Zener Voltage (Note 2)			Zener Impedance (Note 3)			lote 3)	Leakage Current		
Device [†]	Device	,	V _Z (Volts) @ I _{ZT} Z _{ZT} @ I _{ZT} Z _{ZK} @ I _{ZK}		∂ I _{ZK}	I _R @ V _R		I _{ZM}			
(Note 1)	Marking	Min	Nom	Мах	mA	Ω	Ω	mA	μ Α Μах	Volts	mA
1N5929BRNG	1N5929R	14.25	15	15.75	25.0	9	600	0.25	1	11.4	100
1N5932BRNG	1N5932R	19.00	20	21.00	18.7	14	650	0.25	1	15.2	75
1N5934BRNG	1N5934R	22.80	24	25.20	15.6	19	700	0.25	1	18.2	62

ELECTRICAL CHARACTERISTICS (T₁ = 30°C unless otherwise noted, V_F = 1.5 V Max @ I_F = 200 mAdc for all types)

†The "G" suffix indicates Pb-Free package available.

1. TOLERANCE AND TYPE NUMBER DESIGNATION

Tolerance designation – device tolerance of \pm 5% are indicated by a "B" suffix. 2. ZENER VOLTAGE (V_Z) MEASUREMENT

ON Semiconductor guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature (T₁) at 30°C ±1°C, 3/8" from the diode body.
 3. ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from 60 seconds AC voltage, which results when an AC current having an rms value equal to 10% of the DC zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK}.



Figure 1. Power Temperature Derating Curve



Figure 3. Maximum Surge Power

Figure 4. Typical Reverse Leakage

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$\mathsf{T}_{\mathsf{L}} = \theta_{\mathsf{L}\mathsf{A}} \, \mathsf{P}_{\mathsf{D}} + \mathsf{T}_{\mathsf{A}}$$

 θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30–40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$\mathsf{T}_\mathsf{J} = \mathsf{T}_\mathsf{L} + \Delta \mathsf{T}_\mathsf{J}\mathsf{L}$$

 ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for a train of power pulses (L = 3/8 inch) or from Figure 10 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of T_J (ΔT_J) may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta \mathsf{V} = \theta_{\mathsf{VZ}} \, \Delta \mathsf{T}_{\mathsf{J}}$$

 θ_{VZ} , the zener voltage temperature coefficient, is found from Figures 5 and 6.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Data of Figure 2 should not be used to compute surge capability. Surge limitations are given in Figure 3. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 3 be exceeded.



Figure 9. V_Z = 100 thru 400 Volts

Figure 10. Typical Thermal Resistance

PACKAGE DIMENSIONS

AXIAL LEAD CASE 59AB ISSUE O



NOTES: 1. CONTROLLING DIMENSION: INCHES.

- PACKAGE CONTOUR IS OPTIONAL WITHIN DIMENSIONS A AND B. HEAT SLUGS, IF ANY, SHALL BE WITHIN DIMENSION
- B BUT NOT SUBJECT TO ITS MINIMUM VALUE. 3. DIMENSION A DEFINES THE ENTIRE BODY INCLUDING
- HEAT SLUGS. 4. DIMENSION B IS MEASURED AT THE MAXIMUM DIAMETER OF THE RODY.
- OF THE BODY. 5. POLARITY SHALL BE DENOTED BY A CATHODE BAND.
- LEAD DIAMETER, D. IS NOT CONTROLLED IN ZONE F.
 ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41
- ALL ROLES AND NOTES ASSOCIATED WITH JEDEC DO-41
 OUTLINE SHALL APPLY

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.161	0.205	4.10	5.20		
В	0.079	0.106	2.00	2.70		
D	0.028	0.034	0.71	0.86		
F		0.050		1.27		
ĸ	0.540		13.70			

STYLE 1:

PIN 1. CATHODE (POLARITY BAND) 2. ANODE

SURMETIC is a trademark of Semiconductor Components Industries, LLC (SCILLC).

ON Semiconductor and use registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agsociated with such unintended or unauthorized use patent solut. Cwas negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

1N5929BRN/D